

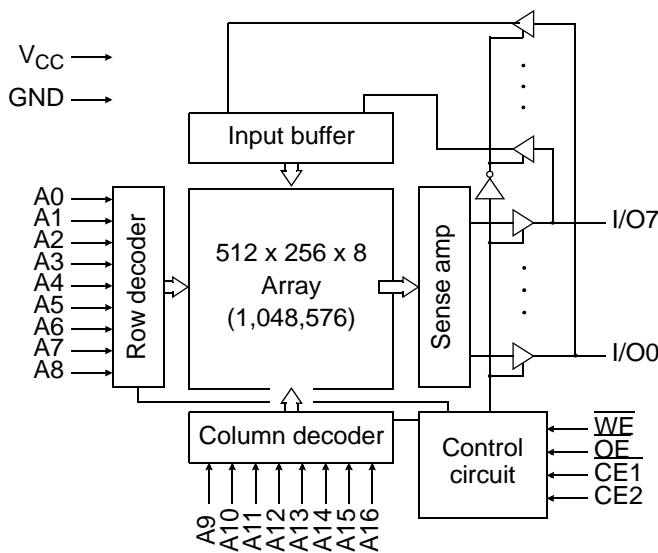


3.3V 128K X 8 CMOS SRAM

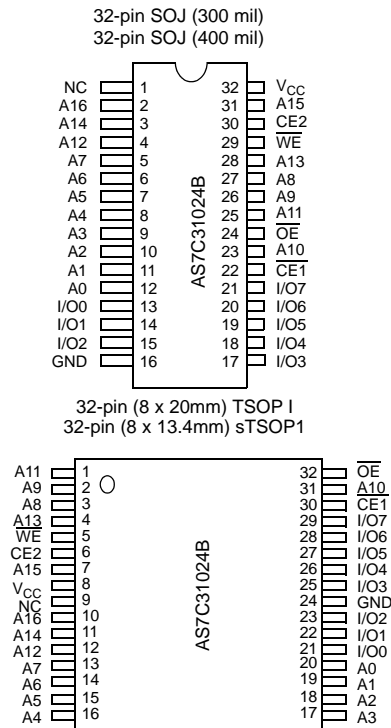
Features

- Industrial and commercial temperatures
- Organization: 131,072 words x 8 bits
- High speed
 - 10/12/15/20 ns address access time
 - 5, 6, 7, 8 ns output enable access time
- Low power consumption: ACTIVE
 - 252 mW / max @ 10 ns
- Low power consumption: STANDBY
 - 18 mW / max CMOS
- 6T 0.18u CMOS technology
- Easy memory expansion with $\overline{CE1}$, $\overline{CE2}$, \overline{OE} inputs
- TTL/LVTTL-compatible, three-state I/O
- 32-pin JEDEC standard packages
 - 300 mil SOJ
 - 400 mil SOJ
 - 8 x 20mm TSOP 1
 - 8 x 13.4mm sTSOP 1
- ESD protection \geq 2000 volts
- Latch-up current \geq 200 mA

Logic block diagram



Pin arrangement



Selection guide

| | -10 | -12 | -15 | -20 | Unit |
|-----------------------------------|-----|-----|-----|-----|------|
| Maximum address access time | 10 | 12 | 15 | 20 | ns |
| Maximum output enable access time | 5 | 6 | 7 | 8 | ns |
| Maximum operating current | 70 | 65 | 60 | 55 | mA |
| Maximum CMOS standby current | 5 | 5 | 5 | 5 | mA |



Functional description

The AS7C31024B is a high performance CMOS 1,048,576-bit Static Random Access Memory (SRAM) device organized as 131,072 words x 8 bits. It is designed for memory applications where fast data access, low power, and simple interfacing are desired.

Equal address access and cycle times (t_{AA} , t_{RC} , t_{WC}) of 10/12/15/20 ns with output enable access times (t_{OE}) of 5, 6, 7, 8 ns are ideal for high performance applications. Active high and low chip enables ($\overline{CE1}$, $CE2$) permit easy memory expansion with multiple-bank systems.

When $\overline{CE1}$ is high or $CE2$ is low, the device enters standby mode. If inputs are still toggling, the device will consume I_{SB} power. If the bus is static, then full standby power is reached (I_{SB1}). For example, the AS7C31024B is guaranteed not to exceed 18 mW under nominal full standby conditions.

A write cycle is accomplished by asserting write enable (\overline{WE}) and both chip enables ($\overline{CE1}$, $CE2$). Data on the input pins I/O0 through I/O7 is written on the rising edge of \overline{WE} (write cycle 1) or the active-to-inactive edge of $\overline{CE1}$ or $CE2$ (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable (\overline{OE}) or write enable (\overline{WE}).

A read cycle is accomplished by asserting output enable (\overline{OE}) and both chip enables ($\overline{CE1}$, $CE2$), with write enable (\overline{WE}) high. The chip drives I/O pins with the data word referenced by the input address. When either chip enable or output enable is inactive, or write enable is active, output drivers stay in high-impedance mode.

Absolute maximum ratings

| Parameter | Symbol | Min | Max | Unit |
|---|------------|-------|-----------------|------|
| Voltage on V_{CC} relative to GND | V_{t1} | -0.50 | +5.0 | V |
| Voltage on any pin relative to GND | V_{t2} | -0.50 | $V_{CC} + 0.50$ | V |
| Power dissipation | P_D | – | 1.0 | W |
| Storage temperature (plastic) | T_{stg} | -65 | +150 | °C |
| Ambient temperature with V_{CC} applied | T_{bias} | -55 | +125 | °C |
| DC current into outputs (low) | I_{OUT} | – | 20 | mA |

Note: Stresses greater than those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth table

| $\overline{CE1}$ | $CE2$ | \overline{WE} | \overline{OE} | Data | Mode |
|------------------|-------|-----------------|-----------------|-----------|----------------------------------|
| H | X | X | X | High Z | Standby (I_{SB} , I_{SB1}) |
| X | L | X | X | High Z | Standby (I_{SB} , I_{SB1}) |
| L | H | H | H | High Z | Output disable (I_{CC}) |
| L | H | H | L | D_{OUT} | Read (I_{CC}) |
| L | H | L | X | D_{IN} | Write (I_{CC}) |

Key: X = don't care, L = low, H = high



Recommended operating conditions

| Parameter | Symbol | Min | Nominal | Max | Unit | |
|-------------------------------|------------|-------|---------|----------------|------|----|
| Supply voltage | V_{CC} | 3.0 | 3.3 | 3.6 | V | |
| Input voltage | V_{IH} | 2.0 | – | $V_{CC} + 0.5$ | V | |
| | V_{IL} | -0.5 | – | 0.8 | V | |
| Ambient operating temperature | commercial | T_A | 0 | – | 70 | °C |

$V_{IL} = -1.0V$ for pulse width less than 5ns

$V_{IH} = V_{CC} + 1.5V$ for pulse width less than 5ns

DC operating characteristics (over the operating range)¹

| Parameter | Sym | Test conditions | -10 | | -12 | | -15 | | -20 | | Unit |
|--------------------------------|------------|--|-----|-----|-----|-----|-----|-----|-----|-----|---------------|
| | | | Min | Max | Min | Max | Min | Max | Min | Max | |
| Input leakage current | $ I_{LI} $ | $V_{CC} = \text{Max}, V_{IN} = \text{GND to } V_{CC}$ | – | 1 | – | 1 | – | 1 | – | 1 | μA |
| Output leakage current | $ I_{LO} $ | $V_{CC} = \text{Max}, \overline{CE1} = V_{IH}$ or $CE2 = V_{IL}, V_{OUT} = \text{GND to } V_{CC}$ | – | 1 | – | 1 | – | 1 | – | 1 | μA |
| Operating power supply current | I_{CC} | $V_{CC} = \text{Max}, \overline{CE1} \leq V_{IL},$ $CE2 \geq V_{IH}, f = f_{\text{Max}},$ $I_{OUT} = 0 \text{ mA}$ | – | 70 | – | 65 | – | 60 | – | 55 | mA |
| Standby power supply current | I_{SB} | $V_{CC} = \text{Max}, \overline{CE1} \geq V_{IH}$ and/or $CE2 \leq V_{IL}, f = f_{\text{Max}}$ | – | 30 | – | 25 | – | 20 | – | 20 | mA |
| | I_{SB1} | $V_{CC} = \text{Max}, \overline{CE1} \geq V_{CC} - 0.2V$ and/ or $CE2 \leq 0.2V$ $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V, f = 0$ | – | 5 | – | 5 | – | 5 | – | 5 | |
| Output voltage | V_{OL} | $I_{OL} = 8 \text{ mA}, V_{CC} = \text{Min}$ | – | 0.4 | – | 0.4 | – | 0.4 | – | 0.4 | V |
| | V_{OH} | $I_{OH} = -4 \text{ mA}, V_{CC} = \text{Min}$ | 2.4 | – | 2.4 | – | 2.4 | – | 2.4 | – | V |

Capacitance ($f = 1 \text{ MHz}, T_a = 25 \text{ }^\circ\text{C}, V_{CC} = \text{NOMINAL}$)²

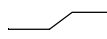
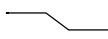

| Parameter | Symbol | Signals | Test conditions | Max | Unit |
|-------------------|-----------|---------------------|-------------------------|-----|------|
| Input capacitance | C_{IN} | A, CE1, CE2, WE, OE | $V_{IN} = 0V$ | 5 | pF |
| I/O capacitance | $C_{I/O}$ | I/O | $V_{IN} = V_{OUT} = 0V$ | 7 | pF |



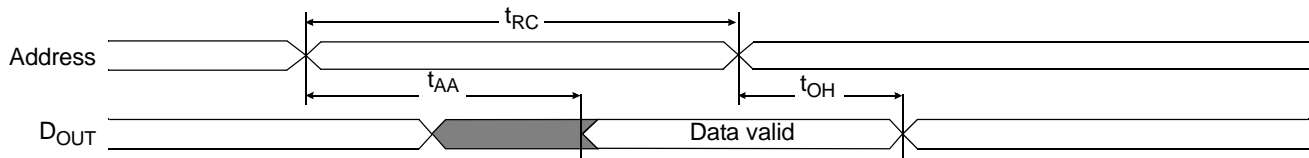
Read cycle (over the operating range)^{3,9,12}

| Parameter | Symbol | -10 | | -12 | | -15 | | -20 | | Unit | Notes |
|---|------------|-----|-----|-----|-----|-----|-----|-----|-----|------|----------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | | |
| Read cycle time | t_{RC} | 10 | – | 12 | – | 15 | – | 20 | | ns | |
| Address access time | t_{AA} | – | 10 | – | 12 | – | 15 | – | 20 | ns | 3 |
| Chip enable ($\overline{CE1}$) access time | t_{ACE1} | – | 10 | – | 12 | – | 15 | – | 20 | ns | 3, 12 |
| Chip enable ($\overline{CE2}$) access time | t_{ACE2} | – | 10 | – | 12 | – | 15 | – | 20 | ns | 3, 12 |
| Output enable (\overline{OE}) access time | t_{OE} | – | 5 | – | 6 | – | 7 | – | 8 | ns | |
| Output hold from address change | t_{OH} | 3 | – | 3 | – | 3 | – | 3 | – | ns | 5 |
| $\overline{CE1}$ low to output in low Z | t_{CLZ1} | 3 | – | 3 | – | 3 | – | 3 | – | ns | 4, 5, 12 |
| $\overline{CE2}$ high to output in low Z | t_{CLZ2} | 3 | – | 3 | – | 3 | – | 3 | – | ns | 4, 5, 12 |
| $\overline{CE1}$ high to output in high Z | t_{CHZ1} | – | 3 | – | 3 | – | 4 | – | 5 | ns | 4, 5, 12 |
| $\overline{CE2}$ low to output in high Z | t_{CHZ2} | – | 3 | – | 3 | – | 4 | – | 5 | ns | 4, 5, 12 |
| \overline{OE} low to output in low Z | t_{OLZ} | 0 | – | 0 | – | 0 | – | 0 | – | ns | 4, 5 |
| \overline{OE} high to output in high Z | t_{OHZ} | – | 5 | – | 6 | – | 7 | – | 8 | ns | 4, 5 |
| Power up time | t_{PU} | 0 | – | 0 | – | 0 | – | 0 | – | ns | 4, 5, 12 |
| Power down time | t_{PD} | – | 10 | – | 12 | – | 15 | – | 20 | ns | 4, 5, 12 |

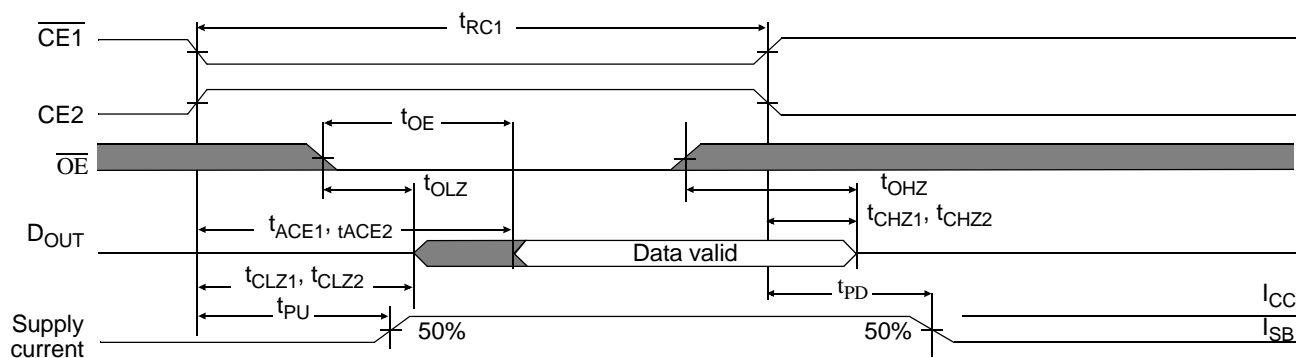
Key to switching waveforms

 Rising input
  Falling input
  Undefined / don't care

Read waveform 1 (address controlled)^{3,6,7,9,12}



Read waveform 2 ($\overline{CE1}$, $\overline{CE2}$, and \overline{OE} controlled)^{3,6,8,9,12}

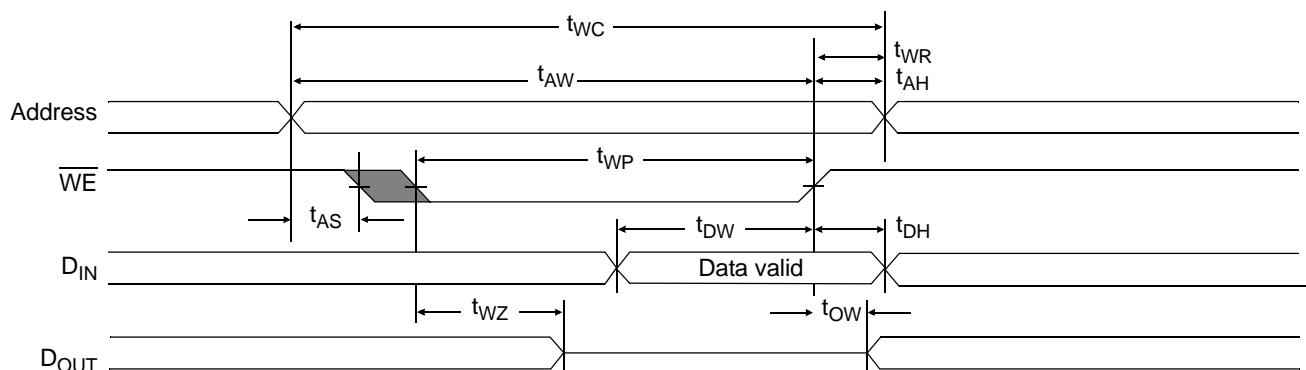




Write cycle (over the operating range)^{11, 12}

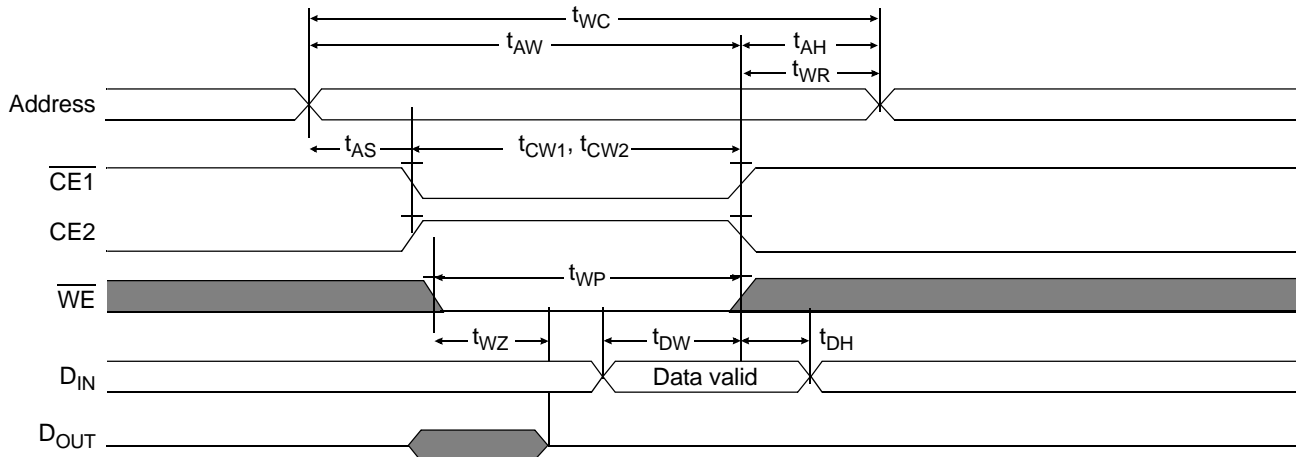
| Parameter | Symbol | -10 | | -12 | | -15 | | -20 | | Unit | Notes |
|----------------------------------|-----------|-----|-----|-----|-----|-----|-----|-----|-----|------|-------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | | |
| Write cycle time | t_{WC} | 10 | – | 12 | – | 15 | – | 20 | – | ns | |
| Chip enable (CE1) to write end | t_{CW1} | 8 | – | 9 | – | 10 | – | 12 | – | ns | 12 |
| Chip enable (CE2) to write end | t_{CW2} | 8 | – | 9 | – | 10 | – | 12 | – | ns | 12 |
| Address setup to write end | t_{AW} | 8 | – | 9 | – | 10 | – | 12 | – | ns | |
| Address setup time | t_{AS} | 0 | – | 0 | – | 0 | – | 0 | – | ns | 12 |
| Write pulse width | t_{WP} | 7 | – | 8 | – | 9 | – | 12 | – | ns | |
| Write recovery time | t_{WR} | 0 | – | 0 | – | 0 | – | 0 | – | ns | |
| Address hold from end of write | t_{AH} | 0 | – | 0 | – | 0 | – | 0 | – | ns | |
| Data valid to write end | t_{DW} | 5 | – | 6 | – | 8 | – | 10 | – | ns | |
| Data hold time | t_{DH} | 0 | – | 0 | – | 0 | – | 0 | – | ns | 4, 5 |
| Write enable to output in high Z | t_{WZ} | – | 5 | – | 6 | – | 7 | – | 8 | ns | 4, 5 |
| Output active from write end | t_{OW} | 1 | – | 1 | – | 1 | – | 1 | – | ns | 4, 5 |

Write waveform 1 (\overline{WE} controlled)^{10,11,12}





Write waveform 2 ($\overline{\text{CE1}}$ and CE2 controlled)^{10,11,12}



AC test conditions

- Output load: see Figure B.
- Input pulse level: GND to 3.0V. See Figure A.
- Input rise and fall times: 2 ns. See Figure A.
- Input and output timing reference levels: 1.5V.

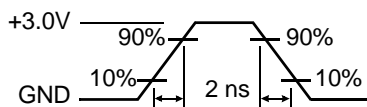


Figure A: Input pulse

Thevenin equivalent:

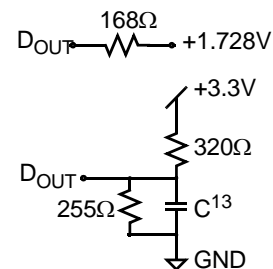


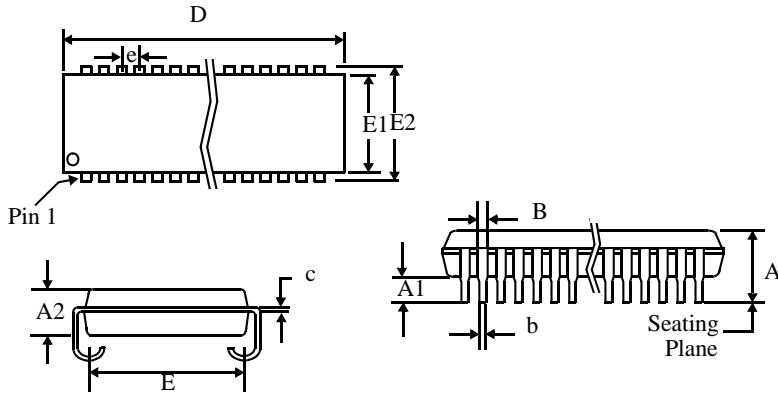
Figure B: 3.3V Output load

Notes

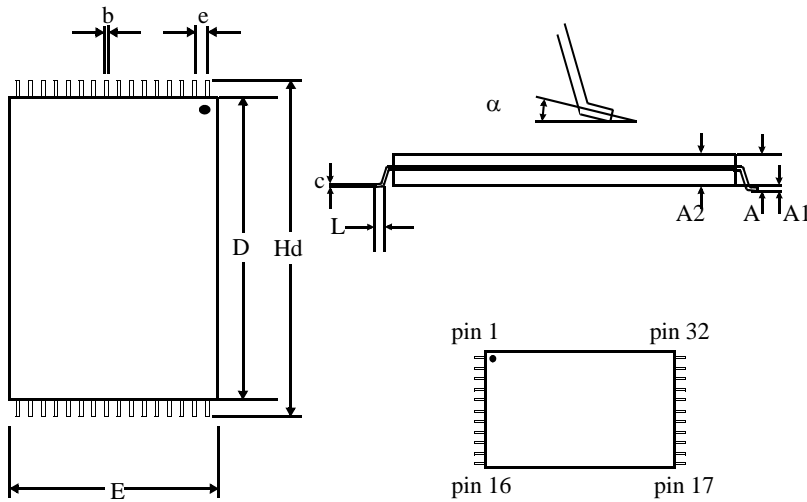
- 1 During V_{CC} power-up, a pull-up resistor to V_{CC} on $\overline{\text{CE1}}$ is required to meet I_{SB} specification.
- 2 This parameter is sampled and not 100% tested.
- 3 For test conditions, see *AC Test Conditions*, Figures A, and B.
- 4 t_{CLZ} and t_{CHZ} are specified with $C_L = 5\text{pF}$, as in Figure C. Transition is measured $\pm 500\text{mV}$ from steady-state voltage.
- 5 This parameter is guaranteed, but not 100% tested.
- 6 $\overline{\text{WE}}$ is high for read cycle.
- 7 $\overline{\text{CE1}}$ and $\overline{\text{OE}}$ are low and CE2 is high for read cycle.
- 8 Address valid prior to or coincident with $\overline{\text{CE1}}$ transition Low.
- 9 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 10 N/A
- 11 All write cycle timings are referenced from the last valid address to the first transitioning address.
- 12 $\overline{\text{CE1}}$ and CE2 have identical timing.
- 13 $C = 30\text{pF}$, except all high Z and low Z parameters where $C = 5\text{pF}$.
- 14 N/A



Package dimensions



| | 32-pin SOJ 300 mil | | 32-pin SOJ 400 mil | |
|----|--------------------|-------|--------------------|-------|
| | Min | Max | Min | Max |
| A | 0.128 | 0.145 | 0.132 | 0.146 |
| A1 | 0.025 | - | 0.025 | - |
| A2 | 0.095 | 0.105 | 0.105 | 0.115 |
| B | 0.026 | 0.032 | 0.026 | 0.032 |
| b | 0.016 | 0.020 | 0.015 | 0.020 |
| c | 0.007 | 0.010 | 0.007 | 0.013 |
| D | 0.820 | 0.830 | 0.820 | 0.830 |
| E | 0.255 | 0.275 | 0.354 | 0.378 |
| E1 | 0.295 | 0.305 | 0.395 | 0.405 |
| E2 | 0.330 | 0.340 | 0.435 | 0.445 |
| e | 0.050 BSC | | 0.050 BSC | |



| | 32-pin TSOP 8x20 mm | |
|-------|---------------------|-------|
| | Min | Max |
| A | - | 1.20 |
| A1 | 0.05 | 0.15 |
| A2 | 0.95 | 1.05 |
| b | 0.17 | 0.27 |
| c | 0.10 | 0.21 |
| D | 18.30 | 18.50 |
| e | 0.50 nominal | |
| E | 7.90 | 8.10 |
| Hd | 19.80 | 20.20 |
| L | 0.50 | 0.70 |
| alpha | 0° | 5° |



Ordering codes

| Package \ Access time | Temp | 10 ns | 12 ns | 15 ns | 20 ns |
|-----------------------|------------|------------------|------------------|------------------|------------------|
| Plastic SOJ, 300 mil | Commercial | AS7C31024B-10TJC | AS7C31024B-12TJC | AS7C31024B-15TJC | AS7C31024B-20TJC |
| Plastic SOJ, 400 mil | Commercial | AS7C31024B-10JC | AS7C31024B-12JC | AS7C31024B-15JC | AS7C31024B-20JC |
| TSOP1 8x20 mm | Commercial | AS7C31024B-10TC | AS7C31024B-12TC | AS7C31024B-15TC | AS7C31024B-20TC |
| sTSOP1 8 x 13.4mm | Commercial | AS7C31024B-10STC | AS7C31024B-12STC | AS7C31024B-15STC | AS7C31024B-20STC |

Note:

Add suffix 'N' to the above part number for lead free parts (Ex. AS7C31024B-10TJCN)

Part numbering system

| AS7C | X | 1024B | -XX | X | X | X |
|----------------|----------------|------------------|----------------|---|---|------------------|
| SRAM prefix | 3 = 3.3 V CMOS | Device number | Access time | Package: T = TSOP1 8x20 mm ST = sTSOP1 8 x 13.4 mm J = SOJ 400 mil TJ = SOJ 300 mil | Temperature range C = Commercial, 0° C to 70° C | N=Lead Free Part |



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